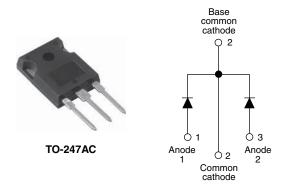


Vishay Semiconductors

# HEXFRED® Ultrafast Soft Recovery Diode, 2 x 16 A



PRODUCT SUMMARY					
Package	TO-247AC				
I <sub>F(AV)</sub>	2 x 16 A				
$V_{R}$	1200 V				
V <sub>F</sub> at I <sub>F</sub>	3.0 V				
t <sub>rr</sub> (typ.)	30 ns				
T <sub>J</sub> max.	150 °C				
Diode variation	Single die				

### **FEATURES**

- Ultrafast and ultrasoft recovery
- Very low I<sub>RRM</sub> and Q<sub>rr</sub>
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified for industrial level





## RoHS

#### **BENEFITS**

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

#### **DESCRIPTION**

VS-HFA32PA120CPbF is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 16 A per leg continuous current, the VS-HFA32PA120CPbF is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I<sub>RRM</sub>) and does not exhibit any tendency to "snap-off" during the t<sub>b</sub> portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA32PA120CPbF is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	V <sub>R</sub>		1200	V		
Maximum continuous forward current per leg		T 100 °C	16			
per device	l <sub>F</sub>	T <sub>C</sub> = 100 °C	32	^		
Single pulse forward current	I <sub>FSM</sub>		190	А		
Maximum repetitive forward current	I <sub>FRM</sub>		64			
Martine and a super distriction	_	T <sub>C</sub> = 25 °C	151	90		
Maximum power dissipation	P <sub>D</sub>	T <sub>C</sub> = 100 °C	60	°C		
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 55 to + 150	W		

### VS-HFA32PA120CPbF

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### **HEXFRED®** Ultrafast Soft Recovery Diode, 2 x 16 A



<b>ELECTRICAL SPECIFICATIONS PER LEG</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	$V_{BR}$	Ι <sub>R</sub> = 100 μΑ		1200	-	-	
		I <sub>F</sub> = 16 A		-	2.5	3.0	V
Maximum forward voltage	$V_{FM}$	$V_{FM}$ $I_F = 32 A$ See fig. 1	-	3.2	3.93		
	I <sub>F</sub> = 16 A, T <sub>J</sub> = 125 °C		1	-	2.3	2.7	
Maximum reverse		V <sub>R</sub> = V <sub>R</sub> rated	Coo fig. 0	-	0.75	20	
leakage current	I <sub>RM</sub>	$T_J = 125$ °C, $V_R = 0.8 \times V_R$ rated	See fig. 2	-	375	2000	μA
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V	See fig. 3	-	27	40	pF
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body		-	8.0	-	nH

<b>DYNAMIC RECOVERY CHARACTERISTICS PER LEG</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, dI_F/dt = 200$	0 A/μs, V <sub>R</sub> = 30 V	-	30	-		
Reverse recovery time See fig. 5, 10	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	90	135	ns	
3ee lig. 3, 10	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	164	245		
Peak recovery current	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 16 A	-	5.8	10	А	
See fig. 6	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C		-	8.3	15		
Reverse recovery charge	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C	dl <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 200 V	-	260	675	nC	
See fig. 7	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C	V <sub>R</sub> = 200 V	-	680	1838	110	
Peak rate of fall of recovery	dI <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	120	-	A/µs	
current during t <sub>b</sub> See fig. 8	dI <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	76	-	Ανμδ	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C	
Thermal resistance, junction to case	R <sub>thJC</sub>		-	-	0.83		
Thermal resistance, junction to ambient	R <sub>thJA</sub>	R <sub>thJA</sub> Typical socket mount		-	80	K/W	
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.50	-		
Weight			-	2.0	-	g	
vveignt			-	0.07	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style TO-247AC (JEDEC)	HFA32PA120C			•	





### **HEXFRED®** Ultrafast Soft Recovery Diode, 2 x 16 A

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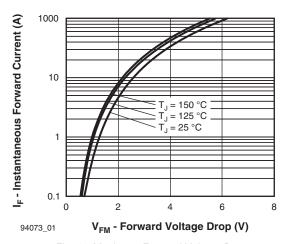


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

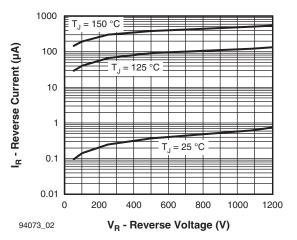


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

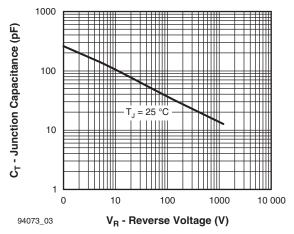


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

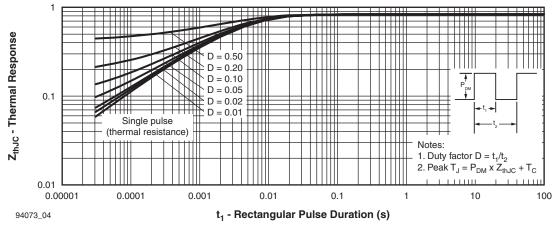


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

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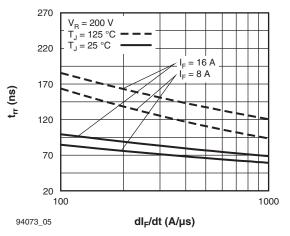


Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt (Per Leg)

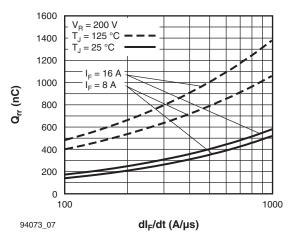


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt (Per Leg)

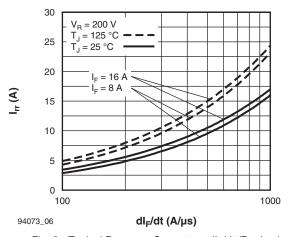


Fig. 6 - Typical Recovery Current vs. dl<sub>F</sub>/dt (Per Leg)

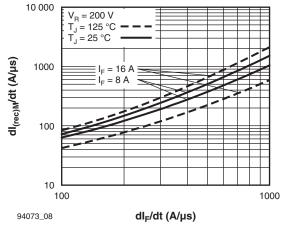


Fig. 8 - Typical dI<sub>(rec)M</sub>/dt vs. dI<sub>F</sub>/dt (Per Leg)



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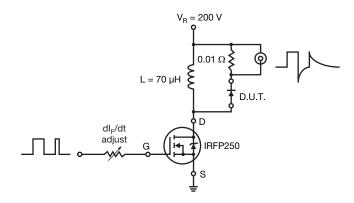
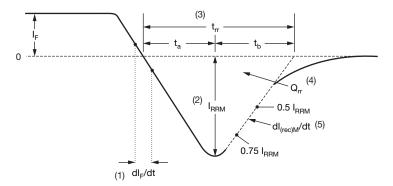


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_F$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{\rm rr}$  area under curve defined by  $\mathbf{t}_{\rm rr}$  and  $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) dI<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 10 - Reverse Recovery Waveform and Definitions

### VS-HFA32PA120CPbF

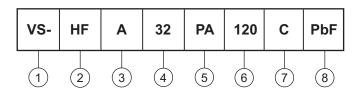
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### **ORDERING INFORMATION TABLE**

Device code



1 - Vishay Semiconductors product

2 - HEXFRED® family

3 - Electron irradiated

- Current rating (32 = 32 A)

**5** - PA = TO-247AC

Voltage rating: (120 = 1200 V)

7 - Circuit configuration

C = Common cathode

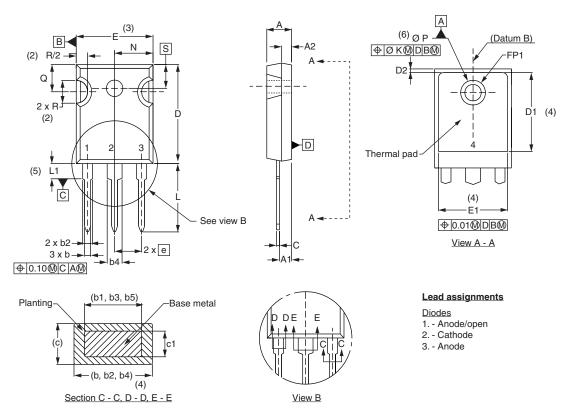
PbF = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95223				
Part marking information	www.vishay.com/doc?95226				



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### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIN	IETERS	INCHES		NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.50	2.49	0.059	0.098	
b	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.37	0.065	0.094	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
С	0.38	0.86	0.015	0.034	
c1	0.38	0.76	0.015	0.030	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

SYMBOL	MILLIN	IETERS	INCHES		NOTES
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.30	0.020	0.051	
E	15.29	15.87	0.602	0.625	3
E1	13.72	-	0.540	-	
е	5.46	BSC	0.215	BSC	
FK	2.	2.54		010	
L	14.20	16.10	0.559	0.634	
L1	3.71	4.29	0.146	0.169	
N	7.62 BSC		0	.3	
ΦР	3.56	3.66	0.14	0.144	
ФР1	1	6.98	-	0.275	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	1.78	0.216	
S	5.51	BSC	0.217	'BSC	

### **Notes**

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c





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